

**TrenchT2™ HiperFET™**  
**Power MOSFET**
**IXFH150N17T2**  
**IXFT150N17T2**

 N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode


$$V_{DSS} = 175V$$

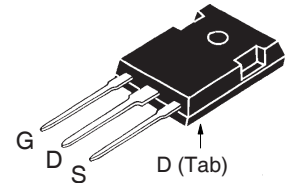
$$I_{D25} = 150A$$

$$R_{DS(on)} \leq 12.0m\Omega$$

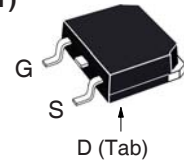
$$t_{rr} \leq 160ns$$

| Symbol     | Test Conditions  | Maximum Ratings |            |
|------------|--|-----------------|------------|
| $V_{DSS}$  | $T_J = 25^\circ C$ to $175^\circ C$                                | 175             | V          |
| $V_{DGR}$  | $T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$          | 175             | V          |
| $V_{GSS}$  | Continuous   | $\pm 20$        | V          |
| $V_{GSM}$  | Transient  | $\pm 30$        | V          |
| $I_{D25}$  | $T_C = 25^\circ C$   | 150             | A          |
| $I_{DM}$   | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 400             | A          |
| $I_A$      | $T_C = 25^\circ C$   | 75              | A          |
| $E_{AS}$   | $T_C = 25^\circ C$   | 1.0             | J          |
| dv/dt      | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 175^\circ C$ | 15              | V/ns       |
| $P_D$      | $T_C = 25^\circ C$   | 880             | W          |
| $T_J$      |  | -55 ... +175    | $^\circ C$ |
| $T_{JM}$   |  | 175             | $^\circ C$ |
| $T_{stg}$  |  | -55 ... +175    | $^\circ C$ |
| $T_L$      | Maximum Lead Temperature for Soldering                             | 300             | $^\circ C$ |
| $T_{SOLD}$ | Plastic Body for 10s   | 260             | $^\circ C$ |
| $M_d$      | Mounting Torque (TO-247)   | 1.13/10         | Nm/lb.in.  |
| Weight     | TO-247   | 6               | g          |
|            | TO-268   | 4               | g          |

TO-247 (IXFH)



TO-268 (IXFT)



G = Gate      D = Drain  
 S = Source    Tab = Drain

**Features**

- High Current Handling Capability
- Fast Intrinsic Diode
- Dynamic dv/dt Rated
- Avalanche Rated
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ , Unless Otherwise Specified) | Characteristic Values |      |                      |
|--------------|---|-----------------------|------|----------------------|
|              |   | Min.                  | Typ. | Max.                 |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 250\mu A$                                      | 175                   |      | V                    |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 1mA$                                       | 2.5                   |      | V                    |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$                                    |                       |      | $\pm 200$ nA         |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 150^\circ C$             |                       |      | 10 $\mu A$<br>1.5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                   | 9.7                   | 12.0 | m $\Omega$           |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)  | Characteristic Values |      |                        |
|--------------|--|-----------------------|------|------------------------|
|              |  | Min.                  | Typ. | Max.                   |
| $g_{fs}$     | $V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1   | 100                   | 165  | S                      |
| $C_{iss}$    | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$   |                       | 14.6 | nF                     |
| $C_{oss}$    |  |                       | 1100 | pF                     |
| $C_{rss}$    |  |                       | 136  | pF                     |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$<br>$R_G = 1\Omega$ (External) |                       | 32   | ns                     |
| $t_r$        |  |                       | 16   | ns                     |
| $t_{d(off)}$ |  |                       | 50   | ns                     |
| $t_f$        |  |                       | 20   | ns                     |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$   |                       | 233  | nC                     |
| $Q_{gs}$     |  |                       | 67   | nC                     |
| $Q_{gd}$     |  |                       | 63   | nC                     |
| $R_{thJC}$   |  |                       |      | $0.17^\circ\text{C/W}$ |
| $R_{thCS}$   | TO-247   | 0.21                  |      | $^\circ\text{C/W}$     |

**Source-Drain Diode**

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)                      | Characteristic Values |      |               |
|----------|--|-----------------------|------|---------------|
|          |  | Min.                  | Typ. | Max.          |
| $I_S$    | $V_{GS} = 0\text{V}$   |                       |      | 150 A         |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$  |                       |      | 600 A         |
| $V_{SD}$ | $I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1   |                       |      | 1.3 V         |
| $t_{rr}$ | $I_F = 75\text{A}, -di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 75\text{V}, V_{GS} = 0\text{V}$ |                       |      | 160 ns        |
| $I_{RM}$ |  |                       | 7.80 | A             |
| $Q_{RM}$ |  |                       | 0.34 | $\mu\text{C}$ |

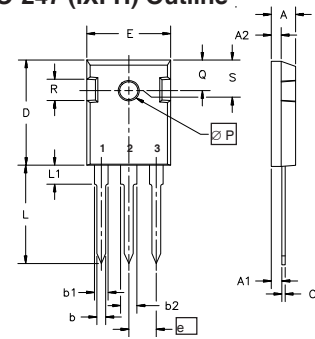
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

**ADVANCE TECHNICAL INFORMATION**

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

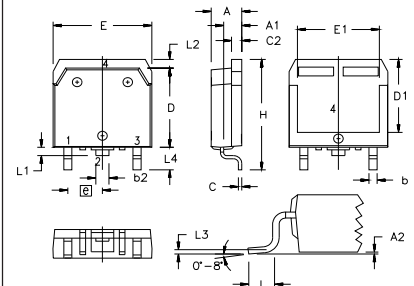
**IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.**

|  |           |           |           |           |              |              |              |              |              |             |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
|  | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
|  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |

**TO-247 (IXFH) Outline**


Terminals: 1 - Gate  
2 - Drain  
3 - Source

| Dim.           | Millimeter |       | Inches |       |
|----------------|------------|-------|--------|-------|
|                | Min.       | Max.  | Min.   | Max.  |
| A              | 4.7        | 5.3   | .185   | .209  |
| A <sub>1</sub> | 2.2        | 2.54  | .087   | .102  |
| A <sub>2</sub> | 2.2        | 2.6   | .059   | .098  |
| b              | 1.0        | 1.4   | .040   | .055  |
| b <sub>1</sub> | 1.65       | 2.13  | .065   | .084  |
| b <sub>2</sub> | 2.87       | 3.12  | .113   | .123  |
| C              | .4         | .8    | .016   | .031  |
| D              | 20.80      | 21.46 | .819   | .845  |
| E              | 15.75      | 16.26 | .610   | .640  |
| e              | 5.20       | 5.72  | 0.205  | 0.225 |
| L              | 19.81      | 20.32 | .780   | .800  |
| L <sub>1</sub> |            | 4.50  |        | .177  |
| ∅P             | 3.55       | 3.65  | .140   | .144  |
| Q              | 5.89       | 6.40  | 0.232  | 0.252 |
| R              | 4.32       | 5.49  | .170   | .216  |
| S              | 6.15       | BSC   | 242    | BSC   |

**TO-268 (IXFT) Outline**


Terminals: 1 - Gate  
2 - Drain  
3 - Source

| SYM            | INCHES |      | MILLIMETERS |       |
|----------------|--------|------|-------------|-------|
|                | MIN    | MAX  | MIN         | MAX   |
| A              | .193   | .201 | 4.90        | 5.10  |
| A <sub>1</sub> | .106   | .114 | 2.70        | 2.90  |
| A <sub>2</sub> | .001   | .010 | 0.02        | 0.25  |
| b              | .045   | .057 | 1.15        | 1.45  |
| b <sub>2</sub> | .075   | .083 | 1.90        | 2.10  |
| C              | .016   | .026 | 0.40        | 0.65  |
| C <sub>2</sub> | .057   | .063 | 1.45        | 1.60  |
| D              | .543   | .551 | 13.80       | 14.00 |
| D <sub>1</sub> | .488   | .500 | 12.40       | 12.70 |
| E              | .624   | .632 | 15.85       | 16.05 |
| E <sub>1</sub> | .524   | .535 | 13.30       | 13.60 |
| e              | .215   | BSC  | 5.45        | BSC   |
| H              | .736   | .752 | 18.70       | 19.10 |
| L              | .094   | .106 | 2.40        | 2.70  |
| L <sub>1</sub> | .047   | .055 | 1.20        | 1.40  |
| L <sub>2</sub> | .039   | .045 | 1.00        | 1.15  |
| L <sub>3</sub> | .010   | BSC  | 0.25        | BSC   |
| L <sub>4</sub> | .150   | .161 | 3.80        | 4.10  |

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

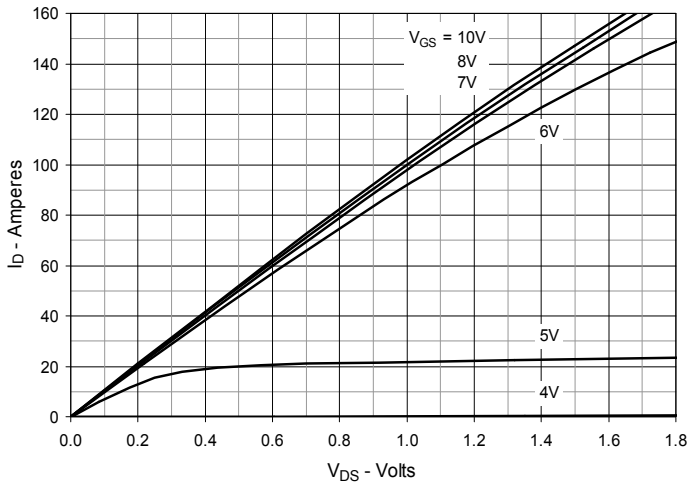


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

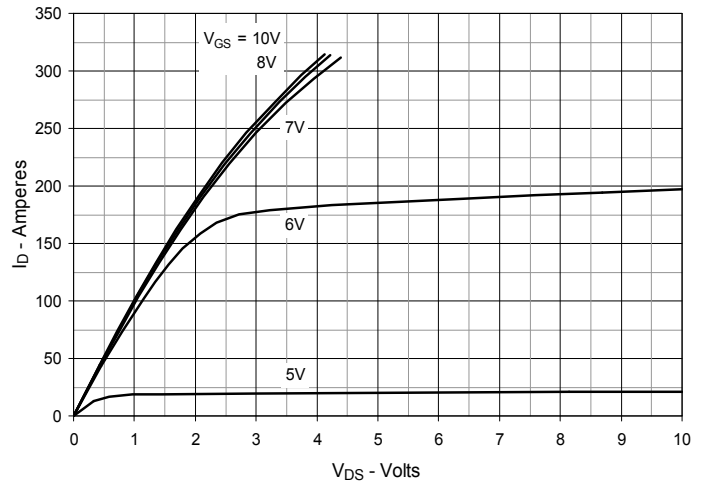


Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$

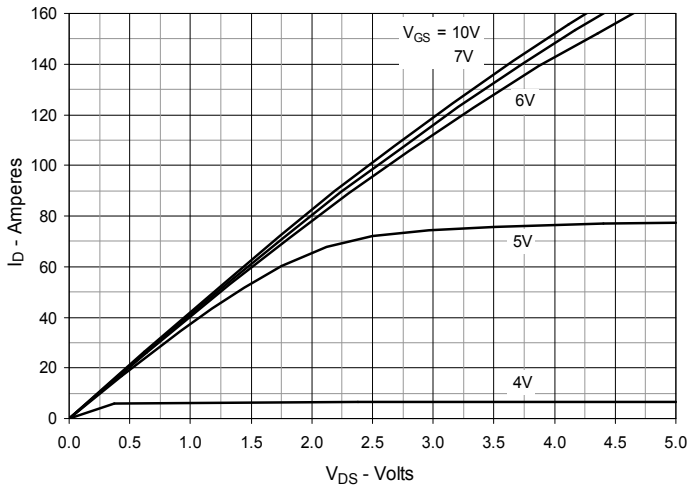


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 75\text{A}$  Value vs. Junction Temperature

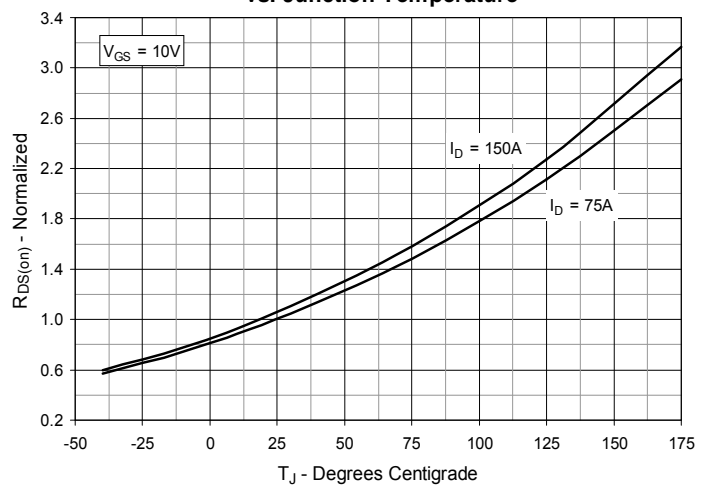


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 75\text{A}$  Value vs. Drain Current

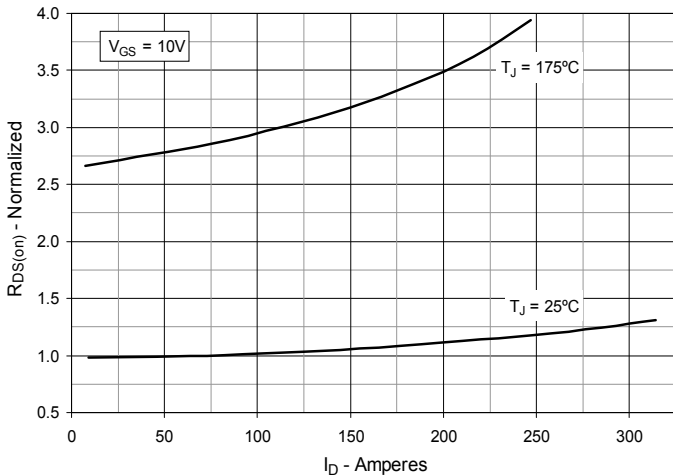
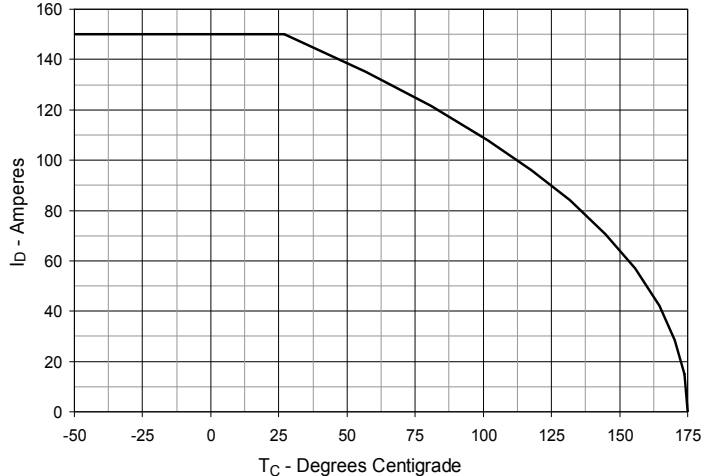
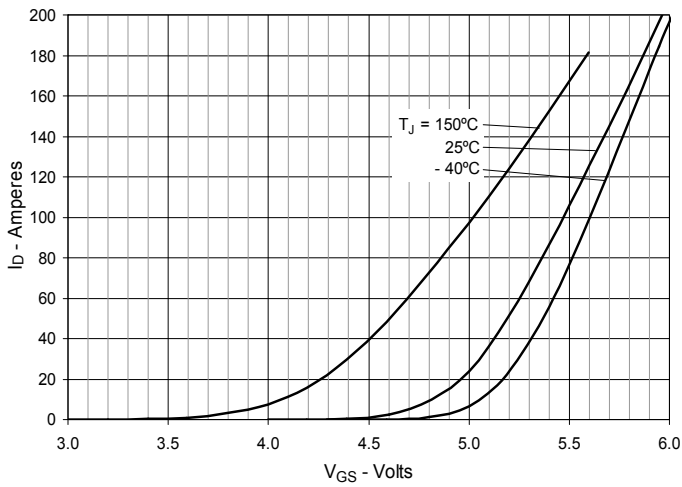


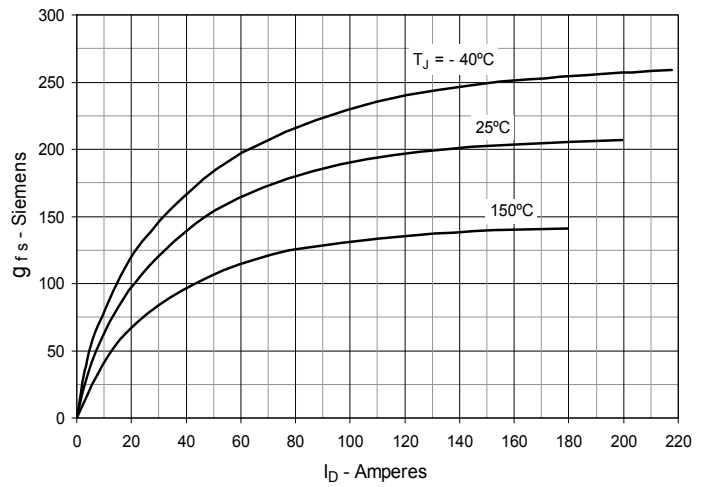
Fig. 6. Drain Current vs. Case Temperature



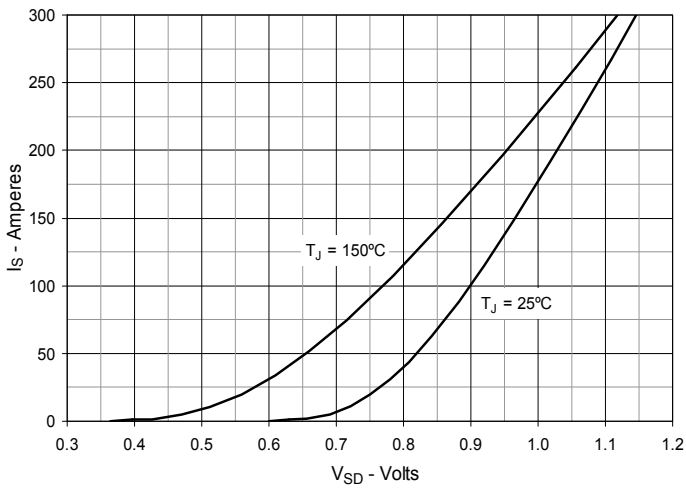
**Fig. 7. Input Admittance**



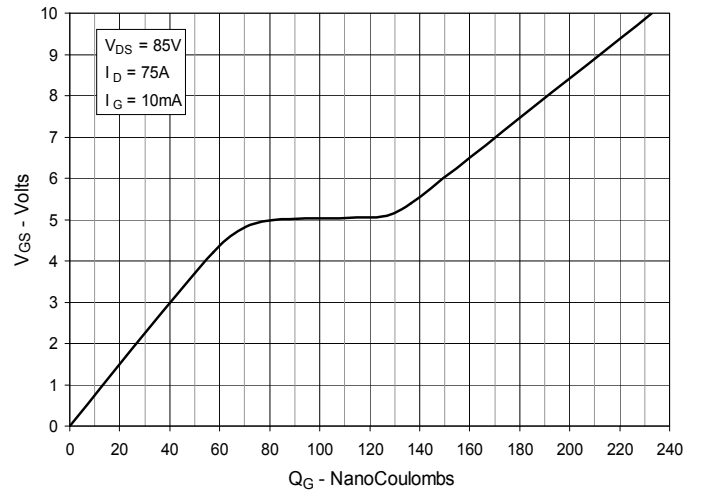
**Fig. 8. Transconductance**



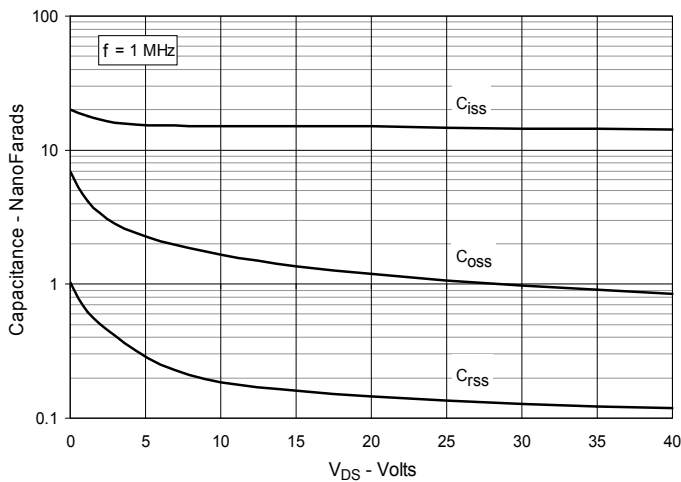
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



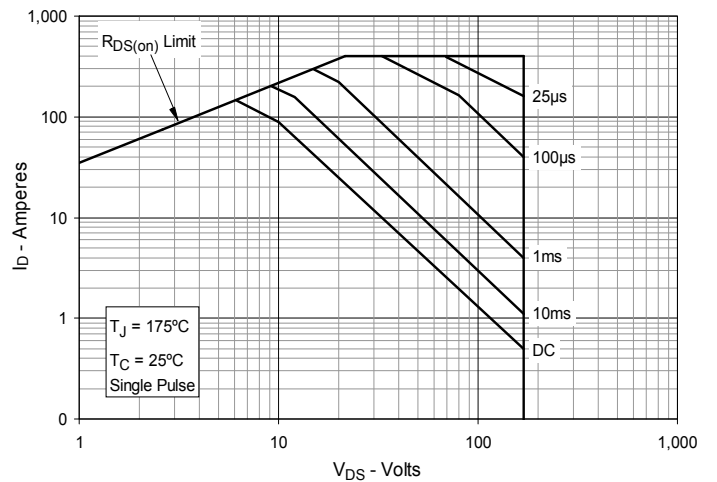
**Fig. 10. Gate Charge**



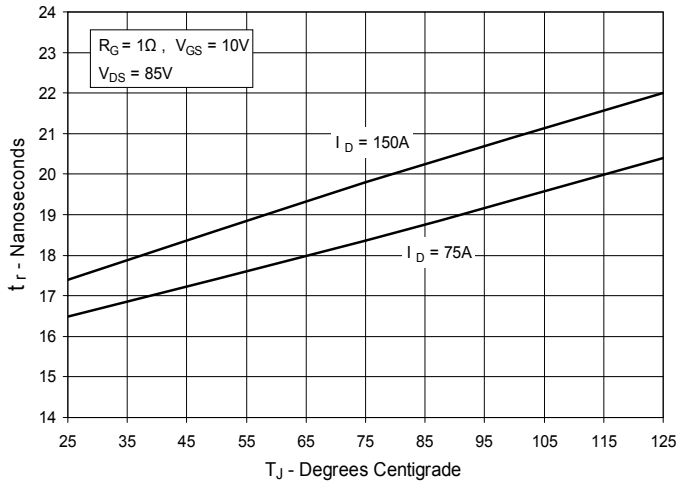
**Fig. 11. Capacitance**



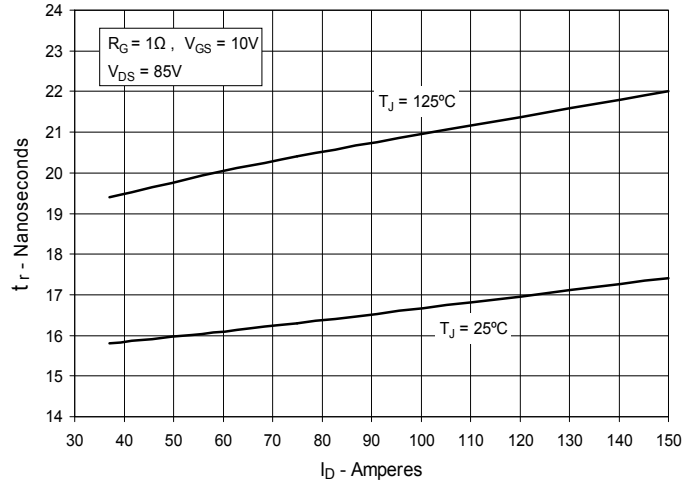
**Fig. 12. Forward-Bias Safe Operating Area**



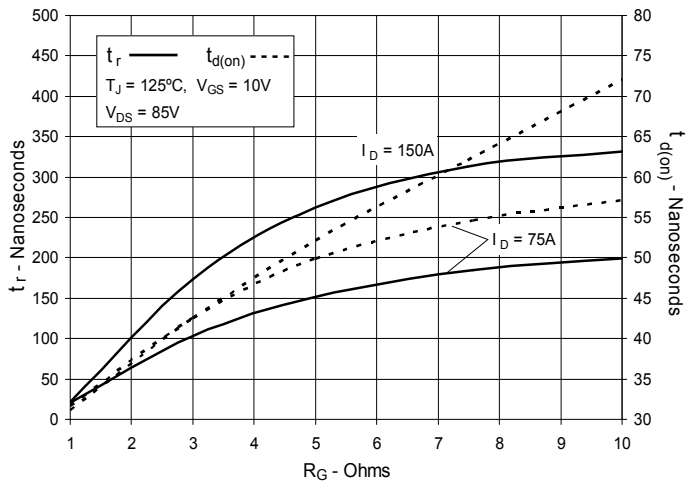
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



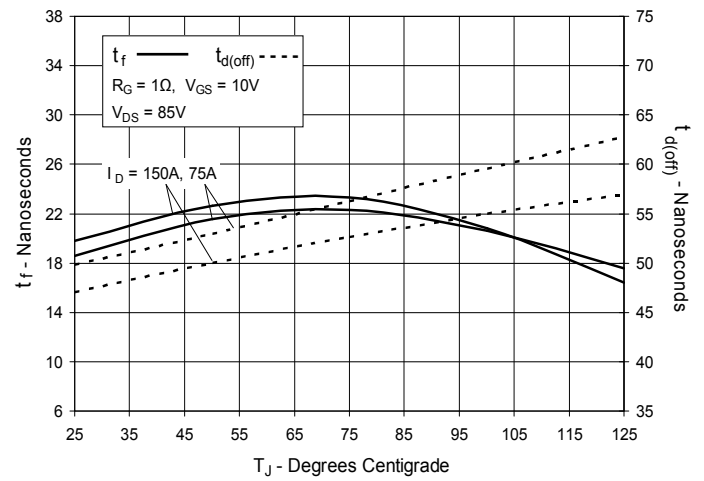
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



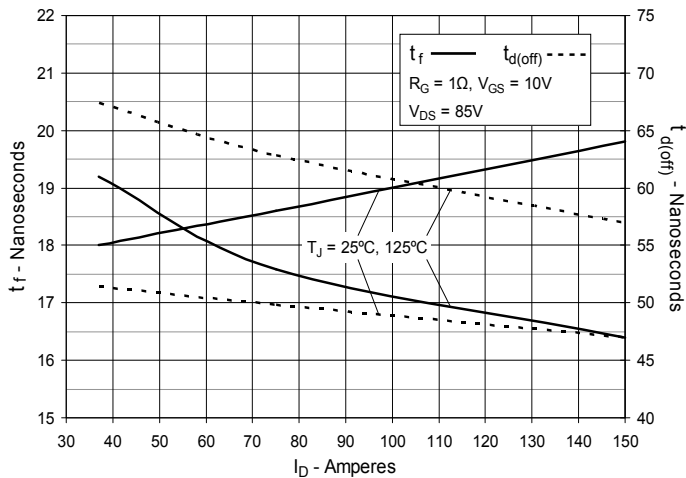
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

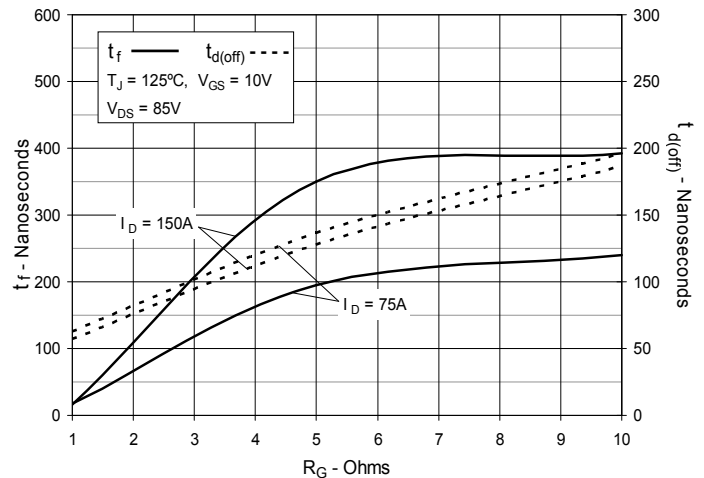
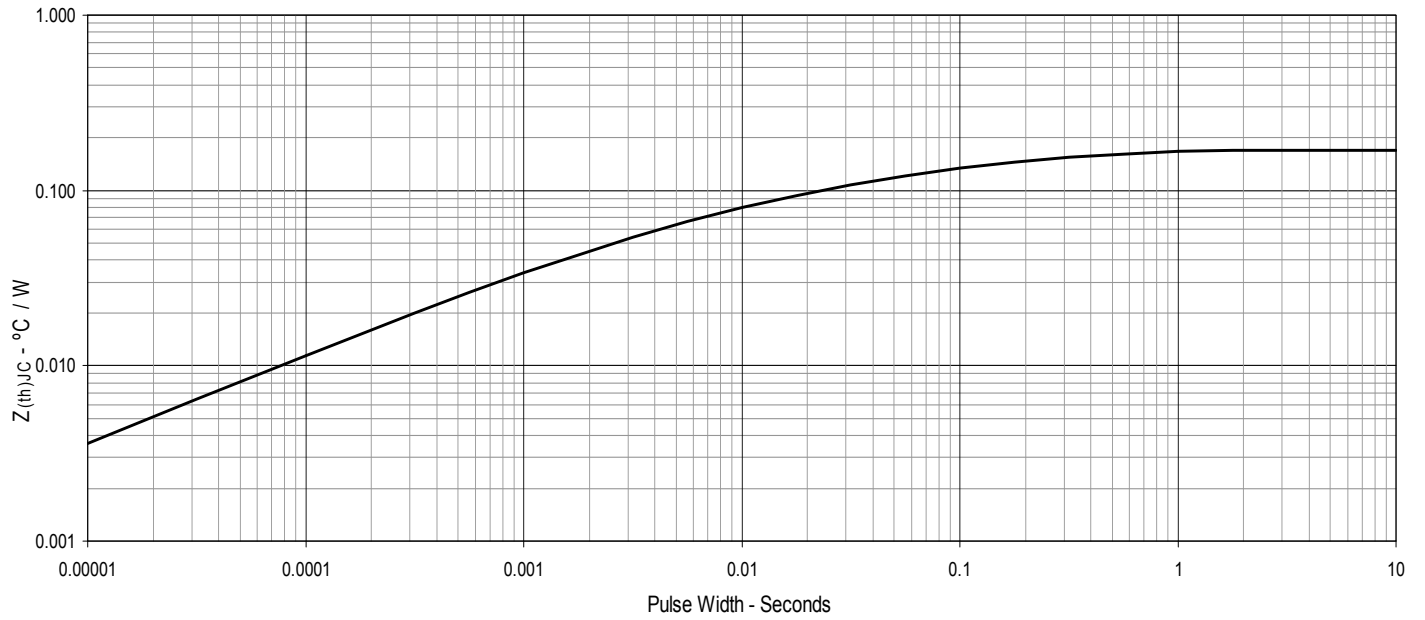


Fig. 19. Maximum Transient Thermal Impedance





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